Top Si thickness after anneal [Å]	Anneal time [min]	Max rate of BOX dissolution [Å/sec]	Dit $x10^{11}$ [$cm^{-2}eV^{-1}$]	Dit control $x10^{11}$ [$cm^{-2}eV^{-1}$]	μe [cm^2/Vs]	μe control [cm^2/Vs]	μh [cm^2/Vs]	μh control [cm^2/Vs]
2300	5	0.01	2	2.5	692	750	202	200
2250	40	0.01	2.4	2.5	661	750	195	200
550	40	0.06	8.3	6	414	520	116	140
400	60	0.08	35	8.5	170	400	55	110
310	6	0.1	-	10	-	350	-	90

FIG. 1

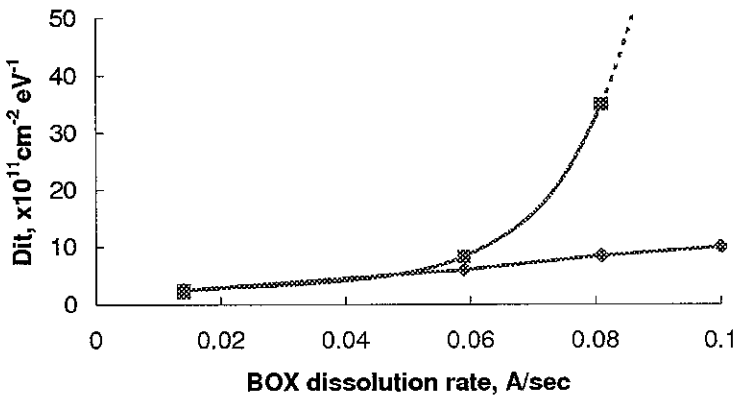


FIG. 2

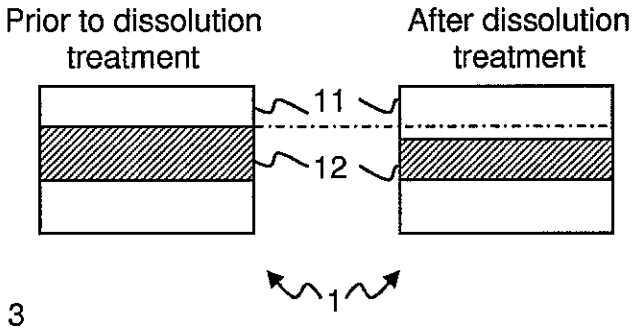

Prior to dissolution treatment
After dissolution treatment
11
12
1

FIG. 3

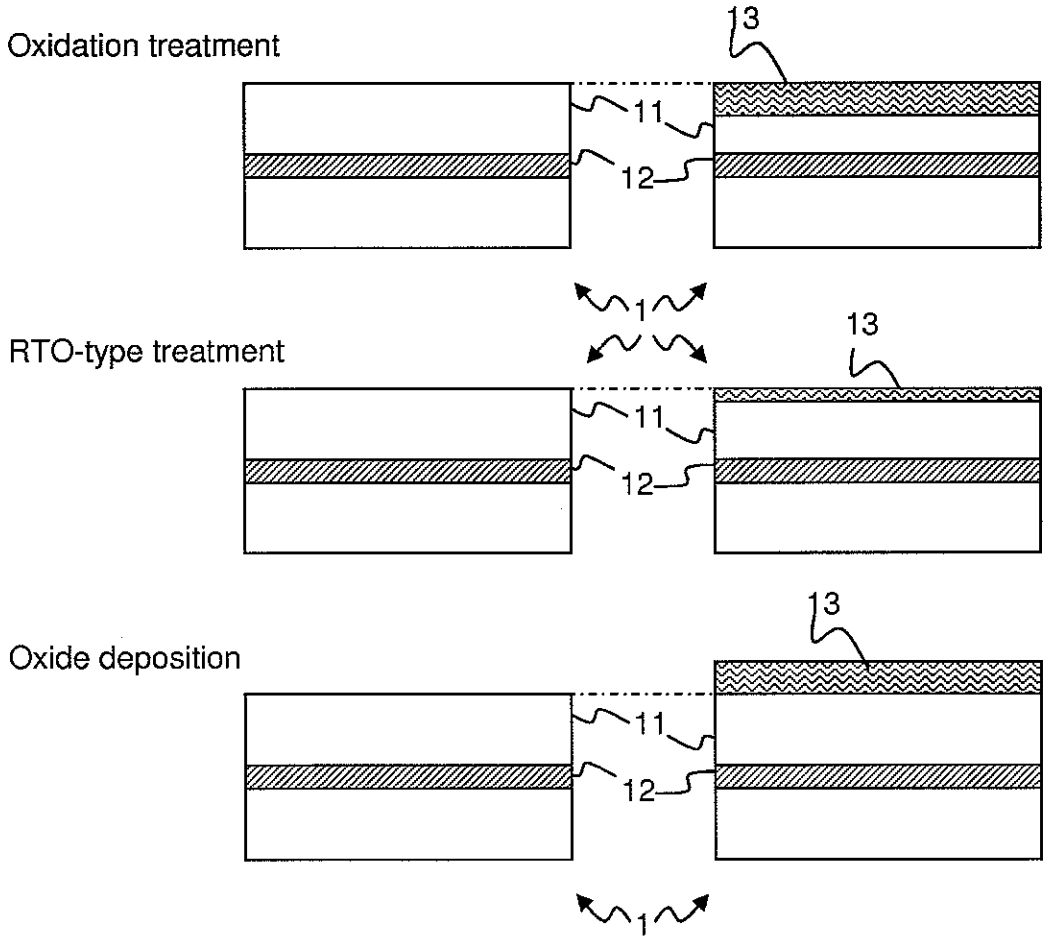

Oxidation treatment
13
11
12
1
RTO-type treatment
13
11
12
Oxide deposition
13
11
12
1

FIG. 4